

IN THE CLAIMS

1. (previously presented) A continuous method for rinsing a cleaned object, which has been cleaned with a cleaning chemical liquid having acidity or alkalinity, comprising the steps of:

    immersing the object in a rinse bath filled therein with pure water;

    continuously feeding pure water to the rinse bath so as to rinse off the cleaning chemical liquid from a surface of the object;

    adding a neutralizing chemical liquid, which has alkalinity or acidity opposite to that of the cleaning chemical liquid, to the pure water in the rinse bath after a predetermined period of time from the start of feeding of the pure water to the rinse bath has elapsed and during the continuous feeding of the pure water to the rinse bath thereby producing a salt by neutralizing the cleaning chemical liquid with the neutralizing chemical liquid; and

    continuously overflowing the rinse bath thereby discharging the residual pure water and the salt from the rinse bath.

2. (original) The method as defined in claim 1, wherein the neutralizing chemical liquid is emitted together with the pure water toward the cleaned object in the rinse bath.

3. (canceled)

4. (canceled)

5. (previously presented) The method as defined in claim 1, wherein the cleaning chemical liquid is one of a sulfuric acid-hydrogen peroxide mixture and a hydrochloric acid-hydrogen

peroxide mixture and the neutralizing chemical liquid is an aqueous ammonia solution.

6. (original) The method as defined in claim 1, wherein the cleaning chemical liquid is an ammonia-hydrogen peroxide mixture and the neutralizing chemical liquid is sulfuric acid.

7. (original) The method as defined in claim 1, wherein the cleaned object is selected from the group consisting of a semiconductor wafer, a silicon wafer and glass components for liquid crystal displays.

8. (previously presented) A continuous method for rinsing a cleaned object which has previously been cleaned with a cleaning chemical having acidity or alkalinity, comprising the steps of:

immersing the cleaned object in a rinse bath containing pure water;

continuously feeding pure water to the rinse bath so as to rinse off residual cleaning chemical from a surface of the cleaned object;

adding a neutralizing chemical which has alkalinity or acidity opposite to that of the cleaning chemical to the pure water in the rinse bath after a predetermined period of time from the start of rinsing by feeding of the pure water to the rinse bath has elapsed; reacting the neutralizing chemical and the residual cleaning chemical to form a salt; continuously overflowing the rinse bath to discharge residual pure water, neutralizing chemical and salt; and removing the object from the rinse bath, the rinsing process being conducted using a single immersion step.

9. (canceled)

10. (canceled)

11. (canceled)

12. (previously presented) The method as defined in claim 8 wherein the cleaning chemical is a sulfuric acid-hydrogen peroxide mixture or a hydrochloric acid-hydrogen peroxide mixture and wherein the neutralizing chemical is an aqueous ammonia solution.

13. (previously presented) The method as defined in claim 1, wherein a resistivity of the pure water in the rinse bath is measured to determine whether the resistivity is restored to a predetermined level to thereby determine the completion of rinsing.

14. (previously presented) The method as defined in claim 13, wherein the predetermined level of the resistivity is set to be 10 MΩ.cm.

15. (previously presented) The method as defined in claim 12, wherein the cleaned object is a semiconductor wafer.

16. (previously presented) The method as defined in claim 12, wherein the cleaned object is a glass component for a liquid crystal display.

17. (new) The method as defined in claim 1, including adding substantially all of said neutralizing chemical to said pure water at one time.

18. (new) The method as defined in claim 8, including adding substantially all of said neutralizing chemical to said pure water at one time.

19. (new) The method as defined in claim 1, including adding said neutralizing chemical so that the resistivity of said pure water in the rinse bath is approximately 10 MΩ x cm.